

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D@25^{\circ}C$
1200V	135mΩ@18V	20A

Feature

- Wide bandgap SiC MOSFET technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed switching
- Low reverse recovery(Qrr)

Application

- Switch Mode Power Supplies
- Renewable Energy
- Motor Drives
- High Voltage DC/DC Converters

Package

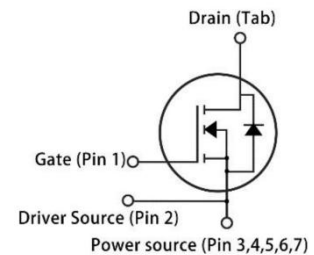


TO-263-7

Marking



Circuit diagram



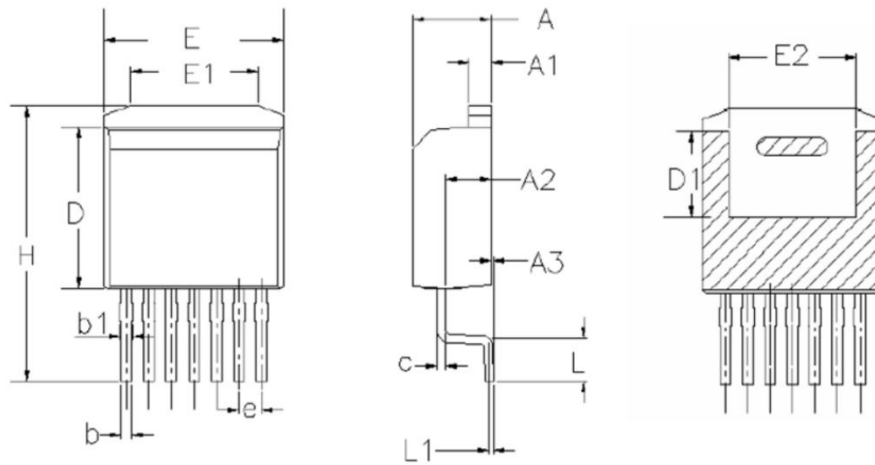
Absolute maximum ratings ($T_c=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Test Condition	Value	Unit
Drain-Source Voltage	V_{DSmax}	$V_{GS} = 0V, I_D = 100\mu A$	1200	V
Gate-Source Voltage	V_{GSmax}	AC ($f > 1\text{ Hz}$)	-10/+25	V
Gate-Source Voltage	V_{GSOP}	Static	-4/+18	V
Continuous Drain Current	I_D	$V_{GS}=18V, T_C=25^{\circ}C$	20	A
	I_D	$V_{GS}=18V, T_C=100^{\circ}C$	14	A
Pulsed Drain Current	$I_{D,pulse}$	Pulse with t_p limited by T_{jmax}	38	A
Power Dissipation	P_D	$T_c=25^{\circ}C$	125	W
Thermal Resistance (Typ)	$R_{\theta JC}$	Junction-to-Case	1.2	$^{\circ}C/W$
Junction Temperature	T_J		-55 ~ +175	$^{\circ}C$
Storage Temperature	T_{STG}		-55 ~ +175	$^{\circ}C$

Electrical characteristics (T_j=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 100μA	1200			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 1200V, V _{GS} = 0V		1	50	μA
Gate-Source leakage current	I _{GSS}	V _{GS} = 18V, V _{DS} = 0V			250	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 2.5mA		2.7		V
		V _{DS} = V _{GS} , I _D = 2.5mA, T _J = 175°C		1.8		
Drain-source on-resistance	R _{DS(on)}	V _{GS} = 18V, I _D = 10A		135	202	mΩ
		V _{GS} = 18V, I _D = 10A, T _J = 175°C		265		
Transconductance	g _{fs}	V _{GS} = 18V, I _D = 10A		6		S
		V _{GS} = 18V, I _D = 10A, T _J = 175°C		5		
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} = 1000V, V _{GS} = 0V, f = 1MHz V _{AC} = 25mV		620		pF
Output Capacitance	C _{oss}			36		
Reverse Transfer Capacitance	C _{rss}			2		
Total Gate Charge	Q _g	V _{DS} = 800V, V _{GS} = -4V/18V, I _D = 10A		40		nC
Gate-Source Charge	Q _{gs}			10		
Gate-Drain Charge	Q _{gd}			15		
Internal Gate Resistance	R _{G(int)}	f = 1 MHz, V _{AC} = 25mV		1		Ω
Source-Drain Diode characteristics						
Diode Forward Current	I _S	V _{GS} = -4V, T _C = 25°C			20	A
Diode Forward voltage	V _{SD}	V _{GS} = -4V, I _{SD} = 3A		3.7		V
		V _{GS} = -4V, I _{SD} = 3A, T _J = 175°C		3.1		
Diode pulse Current	I _{S,pulse}	V _{GS} = -4V, pulse width t _p limited by T _{jmax}		38		A

TO-263-7 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.600	0.169	0.181
A1	1.200	1.400	0.047	0.055
A2	2.400	2.750	0.094	0.108
A3	0.000	0.250	0.000	0.010
b	0.500	0.700	0.020	0.028
b1	0.600	0.900	0.024	0.035
c	0.400	0.600	0.016	0.024
D	8.880	9.280	0.350	0.365
D1	4.650	6.650	0.183	0.262
e	1.270 BSC		0.050 BSC	
E	10.080	10.280	0.397	0.405
E1	6.500	8.300	0.256	0.327
E2	6.820	7.97	0.269	0.314
H	14.800	16.000	0.583	0.630
L	1.900	2.750	0.075	0.108